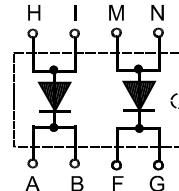


Fast Recovery Epitaxial Diode (FRED)

DSEI 2x61

I_{FAVM} = 2x71 A
V_{RRM} = 200 V
t_{rr} = 35 ns

V _{RSM}	V _{RRM}	Type
V	V	
200	200	DSEI 2x 61-02P



D5

Symbol	Conditions	Maximum Ratings (per diode)		
I _{FRMS}	T _{VJ} = T _{VJM}	100	A	
I _{FAVM} ①	T _C = 85°C; rectangular; d = 0.5	71	A	
I _{FRM}	t _p < 10 µs; rep. rating; pulse width limited by T _{VJM}	800	A	
I _{FSM}	T _{VJ} = 45°C; t = 10 ms (50 Hz), sine	950	A	
T _{VJ}		-40...+150	°C	
T _{VJM}		150	°C	
T _{stg}		-40...+150	°C	
P _{tot}	T _C = 25°C	150	W	
V _{ISOL}	50/60 Hz, RMS	2500	V~	
	I _{ISOL} ≤ 1 mA	3000	V~	
M _d	Mounting torque (M4)	1.5 - 2.0 14 - 18	Nm lb.in.	
Weight		18	g	
Symbol	Conditions	Characteristic Values (per diode)		
		typ.	max.	
I _R	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 25°C V _R = 0.8 • V _{RRM} T _{VJ} = 125°C V _R = 0.8 • V _{RRM}	50 40 11	µA µA mA	
V _F	I _F = 60 A; T _{VJ} = 150°C T _{VJ} = 25°C	0.88 1.08	V V	
V _{T0}	For power-loss calculations only	0.7	V	
r _T	T _{VJ} = T _{VJM}	3.0	mΩ	
R _{thJC}		0.05	0.8	K/W
R _{thCK}				K/W
t _{rr}	I _F = 1 A; -di/dt = 200 A/µs V _R = 30 V; T _{VJ} = 25°C	35	50	ns
I _{RM}	V _R = 100 V; I _F = 60 A; -di _F /dt = 200 A/µs T _{VJ} = 100°C	8	10	A
d _s	Creeping distance on surface	min. 11.2	mm	
d _a	Creeping distance in air	min. 11.2	mm	
a	Allowable acceleration	max. 50	m/s ²	

① I_{FAVM} rating includes reverse blocking losses at T_{VJM}, V_R = 0.8 V_{RRM}, duty cycle d = 0.5
Data according to IEC 60747

Features

- 2 independent FRED in 1 package
- Isolation voltage 3000 V~
- Planar passivated chips
- Leads suitable for PC board soldering
- Very short recovery time
- Soft recovery behaviour

Applications

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- Low noise switching
- Small and light weight

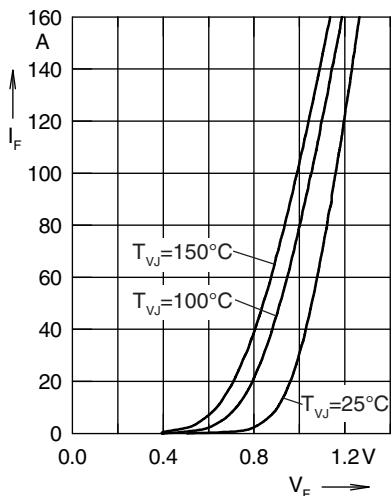


Fig. 1 Forward current I_F versus V_F

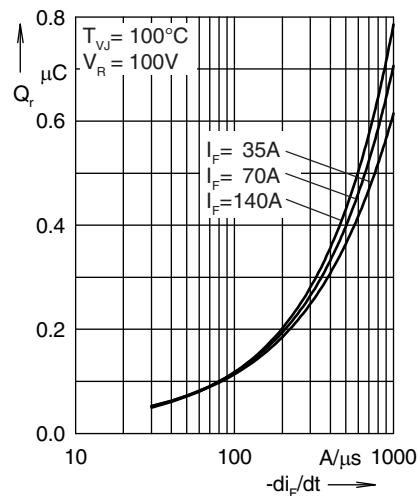


Fig. 2 Typ. reverse recovery charge Q_r versus $-di_F/dt$

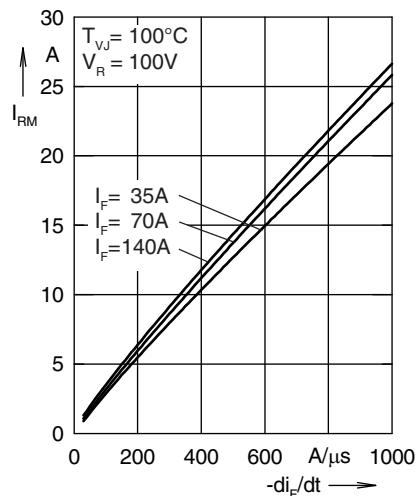


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

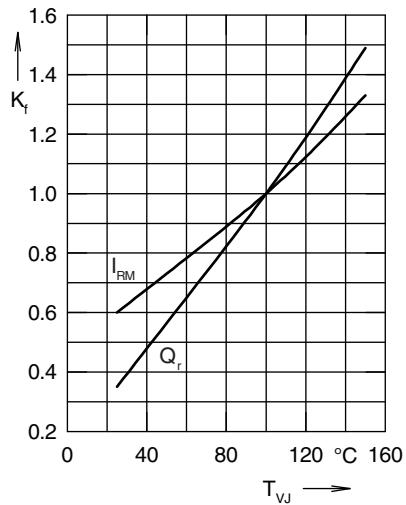


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

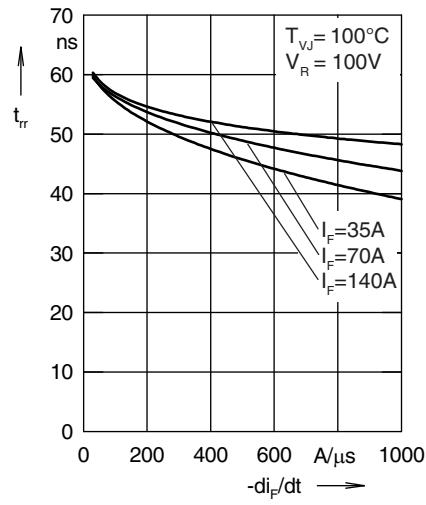


Fig. 5 Typ. recovery time t_{rr}
versus $-dI_F/dt$

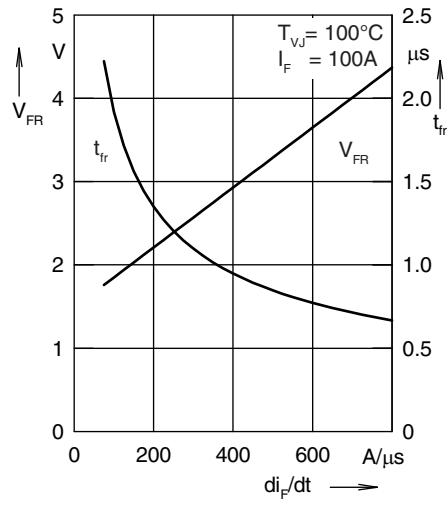


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

Dimensions

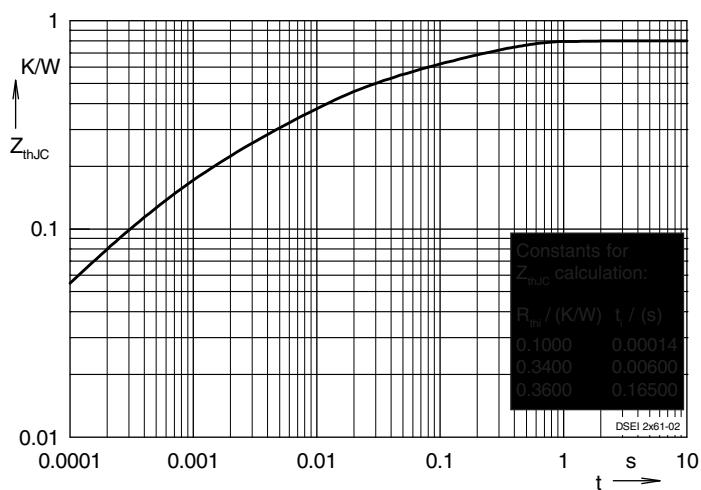


Fig. 7 Transient thermal impedance junction to case

